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# **Schottky Barrier Diode**

Qualified per MIL-PRF-19500/444

<u>Qualified Levels:</u> JAN, JANTX, and JANTXV

#### **DESCRIPTION**

This Schottky barrier diode is metallurgically bonded and offers military grade qualifications for high-reliability applications on "1N" prefixed numbers. This small diode is hermetically sealed and bonded into a DO-35 glass package.

Important: For the latest information, visit our website <a href="http://www.microsemi.com">http://www.microsemi.com</a>.

#### **FEATURES**

- JEDEC registered 1N5711-1, 1N5712-1, 1N6857-1, and 1N6858-1 numbers.
- Metallurgically bonded.
- JAN, JANTX, JANTXV and commercial qualifications also available per MIL-PRF-19500/444 on "1N" numbers only.

(See Part Nomenclature for all available options).

RoHS compliant versions available (commercial grade only).

#### - no-

- APPLICATIONS / BENEFITS
- · Low reverse leakage characteristics.
- Small size for high density mounting using flexible thru-hole leads (see package illustration).
- ESD sensitive to Class 1.

#### MAXIMUM RATINGS @ 25 °C unless otherwise stated

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	$T_J$ and $T_{STG}$	-65 to +150	ōC
Thermal Resistance, Junction-to-Lead	$R_{\Theta JL}$	250	<sup>o</sup> C/W
@ lead length = 0.375 inch (9.52 mm) from body			
Average Rectified Output Current:			
1N5711 <sup>(1)</sup>	Io	33	mA
DSB2810, DSB5712, 1N5712 & 1N6858 (2)		75	
1N6857 <sup>(3)</sup>		150	
Solder Temperature @ 10 s		260	°C

**NOTES:** 1. At  $T_L = +130$ °C and L = 0.375 inch, derate  $I_O$  to 0 at +150°C.

2. At  $T_L = +110 ^{\circ} C$  and L = 0.375 inch, derate  $I_O$  to 0 at  $+150 ^{\circ} C$ .

3. At  $T_L = +70$ °C and L = 0.375 inch, derate  $I_O$  to 0 at +150°C.

DO-35 (DO-204AH)
Package

Also available in:

UB package (3-pin surface mount) 1N5711UB, 1N5712UB (B, CC, CA)

DO-213AA package

(surface mount) 1N5711UR-1, 1N5712UR-1, 1N6857UR-1, and 1N6858UR-1

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#### **MECHANICAL and PACKAGING**

- CASE: Hermetically sealed glass package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode indicated by band.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: Approximately 0.2 grams.

Series number

table)

(see Electrical Characteristics

See Package Dimensions on last page.

#### PART NOMENCLATURE **JAN** 1N5711 -1 (e3)**Reliability Level RoHS Compliance** JAN = JAN level e3 = RoHS compliant (on JANTX = JANTX level commercial grade only) JANTXV = JANTXV level Blank = non-RoHS compliant CDS (reference JANS)\* Blank = Commercial grade Metallurgically Bonded \*Available only on 1N5711-1 JEDEC type number (see Electrical Characteristics table) **DSB** 2810 (e3)**Diode Schottky Barrier RoHS Compliance** e3 = RoHS compliant

SYMBOLS & DEFINITIONS				
Symbol	Definition			
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.			
f	frequency			
I <sub>R</sub>	Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V <sub>R</sub> .			
Io	Average Rectified Output Current: The Output Current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.			
t <sub>rr</sub>	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.			
$V_{(BR)}$	Breakdown Voltage: A voltage in the breakdown region.			
V <sub>F</sub>	Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current.			
V <sub>R</sub>	Reverse Voltage: A positive dc cathode-anode voltage below the breakdown region.			
V <sub>RWM</sub>	Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV.			

Blank = non-RoHS compliant



# ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

TYPE NUMBER	MINIMUM BREAKDOWN VOLTAGE V <sub>(BR)</sub> @ 10 μA	MAXIMUM FORWARD VOLTAGE V <sub>F</sub> @ 1 mA	MAXIMUM FORWARD VOLTAGE V <sub>F</sub> @ I <sub>F</sub>	WORKING PEAK REVERSE VOLTAGE	MAXIMUM REVERSE LEAKAGE CURRENT		$\label{eq:maximum} \begin{aligned} \text{MAXIMUM} \\ \text{CAPACITANCE} \\ @ \ V_R &= 0 \\ \text{VOLTS} \\ f &= 1.0 \ \text{MHz} \\ \end{aligned}$
	Volts	Volts	V @ mA	V (pk)	nA	Volts	pF
1N5711-1	70	0.41	1.0 @ 15	50	200	50	2.0
1N5712-1	20	0.41	1.0 @ 35	16	150	16	2.0
1N6857-1	20	0.35	0.75 @ 35	16	150	16	4.5
1N6858-1	70	0.36	0.65 @ 15	50	200	50	4.5
DSB2810	20	0.41	1.0 @ 35	16	100	15	2.0
DSB5712	20	0.41	1.0 @ 35	16	150	16	2.0



## **GRAPHS**

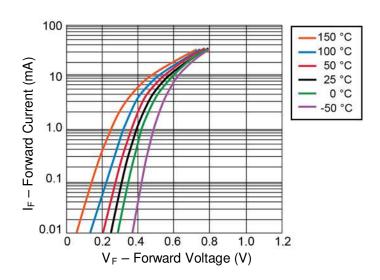


FIGURE 1

<u>I-V Curve showing typical Forward Voltage Variation</u>

Temperature for the 1N5712-1, DSB5712 and DSB2810 Schottky Diodes

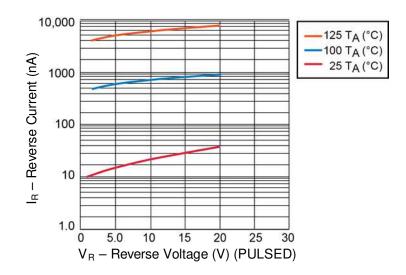


FIGURE 2 1N5712-1, DSB5712 and DSB2810 Typical variation of Reverse Current ( $I_R$ ) vs Reverse Voltage ( $V_R$ ) at Various Temperatures



## **GRAPHS**

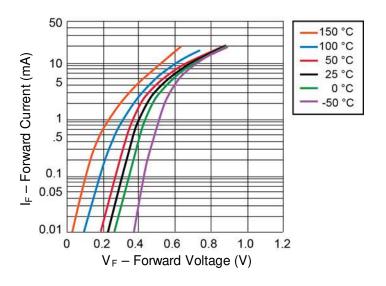


FIGURE 3

I – V curve showing typical Forward Voltage Variation
With Temperature Schottky Diode 1N5711

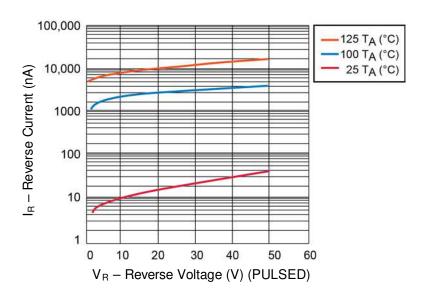


FIGURE 4

1N5711 Typical Variation of Reverse Current (I<sub>R</sub>) vs Reverse Voltage (V<sub>R</sub>)

at Various Temperatures



# **GRAPHS**

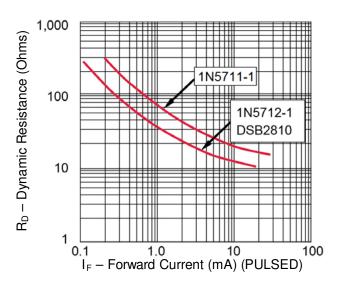
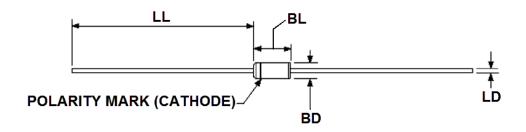


FIGURE 5 Typical Dynamic Resistance ( $R_D$ ) vs Forward Current ( $I_F$ )



## **PACKAGE DIMENSIONS**



#### NOTES:

- 1. Dimensions are in inches. Millimeters are given for information only.
- 2. Dimensions BL and LD includes all components of the diode periphery expect the section of the leads over which the diameter is controlled.
- 3. Dimension BD shall be measured at the largest diameter.
- In accordance with ASME Y1.4M, diameters are equivalents to φx symbology.

	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
BD	0.068	0.076	1.73	1.93	2,3
BL	0.125	0.170	3.18	4.32	2
LD	0.014	0.022	0.36	0.56	
LL	1.000	1.500	25.40	38.10	